

TRIAC BT137

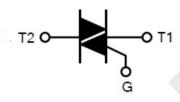
#### **FEATURES**

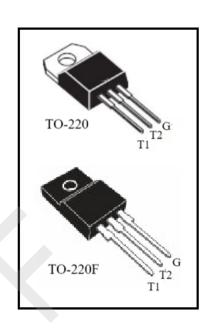
This device of sensitive TRIAC product is a glass passivated device, has a low gate trigger current, high stability in gate trigger current to variation of operating temperature and high off state voltage.

## **APPLICATIONS**

This device is suitable for low power AC switching application, phase control application such as fan speed and temperature modulation control, lighting control and static switching relay.

### SYMBOL:





Tel: +86-755-83677999

## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL		UNIT				
Repetitive Peak Off-State Voltages	V <sub>DRM</sub> , V <sub>RRM</sub>	BT137-600(D/E/F) 600			\/		
		BT137-8	300(D/E/F)	V			
RMS on-State Current	I <sub>T(RMS)</sub>		Α				
Non-Repetitive Peak On-State Current	I <sub>TSM</sub>		Α				
I <sup>2</sup> t for fusing	I <sup>2</sup> t		A <sup>2</sup> s				
	dlT/dt	I	50				
Repetitive rate of rise of on-state		II	50	A /::C			
current after triggering		III	50		A/uS		
		IV	10				
Peak gate current	I <sub>GM</sub>		Α				
Peak Gate Power	$P_{GM}$		W				
Average Gate Power	$P_{G(AV)}$		W				
Operating junction temperature	T <sub>J</sub>	-	$^{\circ}$				
Storage Temperature	T <sub>STG</sub>	-4	$^{\circ}$				



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# **ELECTRICAL CHARACTERISTICS** (TJ=25°C)

Parameter	Symbol	Test Conditions		MIN	MAX			Units
Parameter	Symbol				D	E	F	
Peak Repetitive Forward or	I <sub>DRM</sub>	V <sub>AK</sub> = Rated V <sub>DRM</sub> or			5		uA	
Reverse Blocking Current	I <sub>RRM</sub>	V <sub>RRM</sub> ;						
Gate Trigger Current	I <sub>GT</sub>	$V_D$ =12 $V$ , $R_L$ =100 $\Omega$	I		5	10	25	mA
			II		5	10	25	
			Ш		5	10	25	
			IV		10	25	50	
Gate Trigger Voltage	V <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =100Ω			1.5		V	
Gate Non-Trigger Voltage	$V_{GD}$	$V_D = V_{DRM}, R_L = 3$ $T_j = 125 \text{ °C}$	0.2				V	
Peak Forward On-State Voltage	$V_{TM}$	IT=10A,			1.6		V	
Latch Current I <sub>L</sub>		Ig=1.2Igт	I		10	30	50	- mA
			П		20	40	70	
	IL		III		10	30	50	
			IV		10	30	50	
Holding Current	I <sub>H</sub>	T=0.1A			10	20	40	mA
Critical Rate of Rise of Off-State Voltage	dV/dt	V <sub>D</sub> =67%V <sub>DRM</sub> , T <sub>J</sub> =25°C, Gate open		20		•		V/µs

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